



General Description

The WSR98P06 is the highest performance trench P-Ch MOSFET with extreme high cell density, which provide excellent R_{DSON} and gate charge for most of the synchronous buck converter applications .

The WSR98P06 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

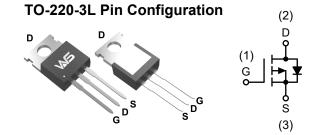
- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Product Summery

BV _{DSS}	R _{DSON}	I _D
-60V	5.2mΩ	-132A

Applications

 Power Management in Desktop Computer or DC/ DC Converters



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	±25	V
Ip	Continuous Drain Current, V _{GS} @ -10V;T _C =25°C	-132	А
טו	Continuous Drain Current, V _{GS} @ -10V;T _C =100°C	-83	Α
ls	Diode Continuous Forward Current	-80	А
I _{AS}	Avalanche Energy, Single pulse ;L=1mH	49	А
E _{AS}	Avalanche Energy, Single pulse;;L=1mH	1200	mJ
I _{DP}	Pulse Drain Current Tested ;Tc=25°C	-264	Α
P _D	Maximum Power Dissipation;T _C =25°C	250	W
r _D	Maximum Power Dissipation;T _C =100°C	100	W
T _{STG}	Storage Temperature Range	-55 to 150	$^{\circ}$
TJ	Operating Junction Temperature Range	-55 to 150	$^{\circ}$

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	55	°C/W	
$R_{ heta JA}$	Thermal Resistance Junction-Ambient ¹ (t ≤10s)		20	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹		0.5	°C/W

Note: *Current limited by bond wire.

Note a : UIS tested and pulse width limited by maximum junction temperature 150 $^{\circ}$ C (initial temperature Tj=25 $^{\circ}$ C).



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-60			V	
$\triangle BV_{DSS}/\triangle T_{J}$	BV _{DSS} Temperature Coefficient	Reference to 25℃, I _D =-1mA		-0.018		V/°C	
D	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-20A		5.2	6.5	mo	
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V _{GS} =-4.5V , I _D =-10A		8.5	11.5	mΩ	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} . I _D =-250uA	-1.3	-1.8	-2.5	V	
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	V _{GS} =V _{DS} , I _D =-250UA		5.04		mV/℃	
ı	Drain Source Leakage Current	V _{DS} =-48V , V _{GS} =0V , T _J =25℃			1	uA	
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-48V , V _{GS} =0V , T _J =55℃			5		
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm 25V$, V_{DS} = $0V$			±100	nA	
gfs	Forward Transconductance	V _{DS} =-5V , I _D =-20A		26.4		S	
Qg	Total Gate Charge (-4.5V)			136			
Q_gs	Gate-Source Charge	V _{DS} =-30V , V _{GS} =-4.5V , I _D =-20A		20		nC	
Q _{gd}	Gate-Drain Charge			33			
T _{d(on)}	Turn-On Delay Time			18			
T _r	Rise Time	V _{DD} =-15V , V _{GS} =-10V ,		20		ns	
$T_{d(off)}$	Turn-Off Delay Time	$R_G=3.3\Omega$, $I_D=-20A$		120			
T _f	Fall Time			200			
C _{iss}	Input Capacitance			6095			
Coss	Output Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz		1080		pF	
C _{rss}	Reverse Transfer Capacitance			430			

Diode Characteristics

Symbol	Parameter Conditions		Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,6}	V _G =V _D =0V , Force Current			-80	Α
I _{SM}	Pulsed Source Current ^{2,6}	V _G =V _D =0V , Force Current			-160	Α
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25℃			-1.2	V
t _{rr}	Reverse Recovery Time	IF=-20A,dI/dt=100A/µs , T _{.i} =25℃		30		nS
Q _{rr}	Reverse Recovery Charge	- π = 20/1, απαί = 100/1/μ3 , 1 j = 20 C		20		nC

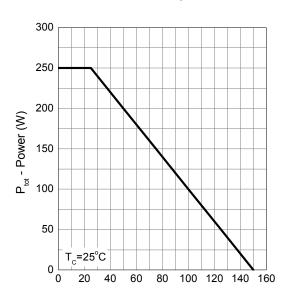
Note:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper,t<10sec.
- 2.The data tested by pulsed , pulse width $\,\leq\,$ 300us , duty cycle $\,\leq\,$ 2%
- 3. The EAS data shows Max. rating . The test condition is V_{DD} =-25V, V_{GS} =-10V,L=0.1mH, I_{AS} =-30A
- 4. The power dissipation is limited by 150 °C junction temperature
- 5.The Min. value is 100% EAS tested guarantee.
- 6. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



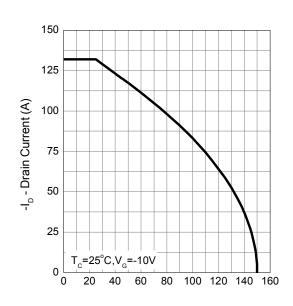
Typical Characteristics

Power Dissipation



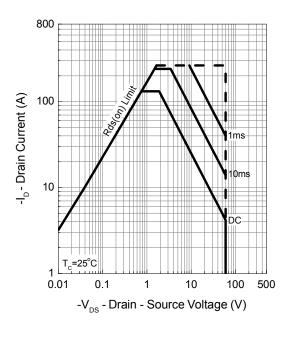
T_J - Junction Temperature (°C)

Drain Current

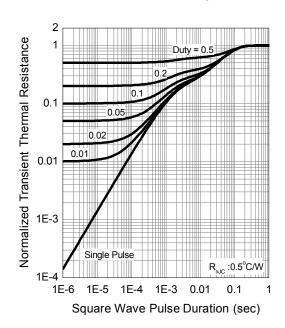


T_J - Junction Temperature (°C)

Safe Operation Area



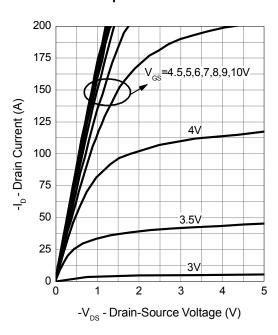
Thermal Transient Impedance



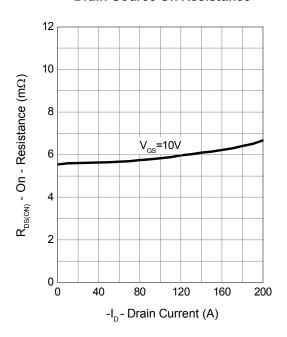


Typical Characteristics

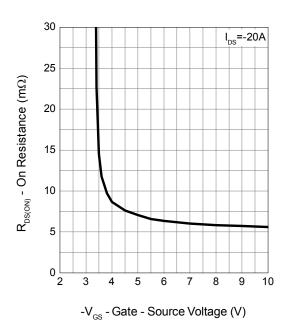
Output Characteristics



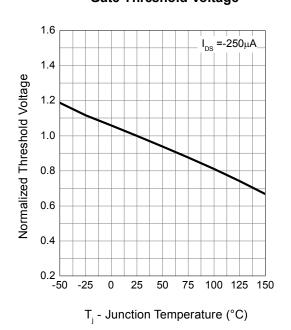
Drain-Source On Resistance



Gate-Source On Resistance



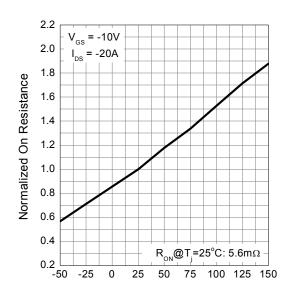
Gate Threshold Voltage





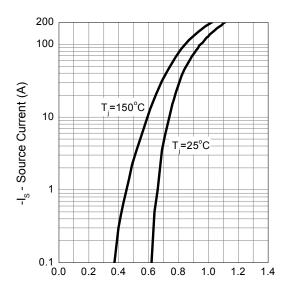
Typical Characteristics

Drain-Source On Resistance



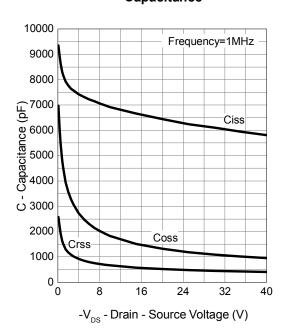
T_i - Junction Temperature (°C)

Source-Drain Diode Forward

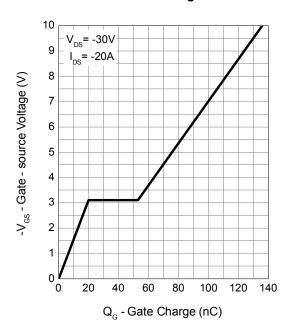


- V_{SD} - Source - Drain Voltage (V)

Capacitance

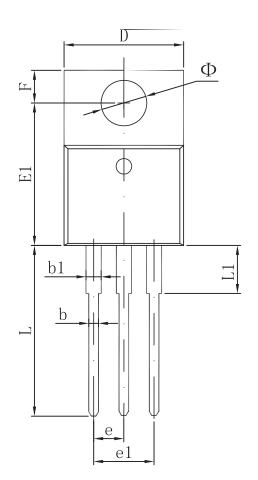


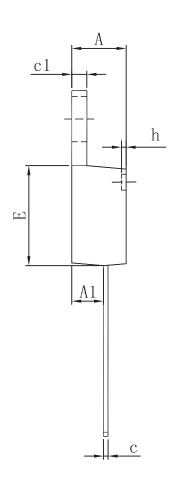
Gate Charge





Packaging information





Cumbal	Dimensions In Millimeters		Dimension	s In Inches
Symbol	Min	Max	Min	Max
A	4.470	4.670	0.176	0.184
A1	2.520	2.820	0.099	0.111
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
С	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
Е	8. 500	8.900	0.335	0.350
E1	12.060	12.460	0.475	0.491
е	2.540 TYP		0.100	TYP
e1	4. 980	5. 180	0.196	0.204
F	2.590	2.890	0.102	0.114
h	0.000	0.300	0.000	0.012
L	13.400	13.800	0.528	0.543
L1	3. 560	3.960	0.140	0.156
Ф	3. 735	3.935	0.147	0.155



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